

IN THE CLAIMS:

Please amend claims 1, 6, and 7, **and add** new claims 8 and 9, as shown in the complete list of claims that is presented below.

1. (currently amended) A semiconductor device, comprising a transistor and surge absorption element formed on the same substrate and connected in parallel, wherein said surge absorption element fulfills first and second conditions, said first condition being that said surge absorption element has a resistance during breakdown operation that is smaller than a resistance of the surge absorption element during breakdown operation of said transistor, and ~~wherein~~ said second condition being that a secondary breakdown current of said surge absorption element is larger than a secondary breakdown current of said transistor.

2. (original) The semiconductor device according to claim 1, wherein the secondary breakdown voltage of said surge absorption element is smaller than the secondary breakdown voltage of said transistor.

3. (original) The semiconductor device according to claim 1, wherein the breakdown voltage of said surge absorption element is smaller than the breakdown voltage of said transistor.

4. (original) The semiconductor device according to claim 3, wherein the secondary breakdown voltage of said surge absorption element is smaller than the secondary breakdown voltage of said transistor.

5. (original) The semiconductor device according to claim 1, wherein the secondary breakdown current of said surge absorption element is larger than a surge current flowing to said surge absorption element.

6. (currently amended) The semiconductor device according to claim 1, ~~characterized in that~~ wherein said transistor is a lateral MOSFET and said ~~[[diode]]~~ surge absorption element is a Zener diode.

7. (currently amended) A semiconductor device constituted by a plurality of transistors, comprising:

an input terminal;

an output terminal;

a voltage source terminal; and

a surge absorption element that is provided in at least one of a circuit location between the input terminal and voltage source terminal, a circuit location between the output terminal and voltage source terminal, and a circuit location between the voltage source terminal and ground;

wherein the surge absorption element and each transistor satisfies at least one of the following relationships:

the surge absorption element has a resistance during breakdown operation that is smaller than a resistance of the surge absorption element during breakdown operation of the transistor,

a secondary breakdown current of the surge absorption element is larger than a secondary breakdown current of the transistor,

the secondary breakdown voltage of the surge absorption element is smaller than the secondary breakdown voltage of the transistor,

the breakdown voltage of the surge absorption element is smaller than the breakdown voltage of the transistor, and

the secondary breakdown current of the surge absorption element is larger than a surge current flowing to the surge absorption element.

8. (new) The semiconductor device of claim 1, wherein said substrate has a resistivity ranging from about 0.3 Ωcm to about 10 Ωcm at a location where said surge absorption element and said transistor are fabricated.

9. (new) The semiconductor device of claim 1, wherein said surge absorption element occupies in an area on said substrate that is not substantially larger than is necessary in order for said surge absorption element to fulfill said first and second conditions.